





N-CHANNEL ENHANCEMENT MODE MOSFET

Features

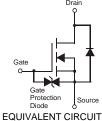
- Low On-Resistance:
 - 3.0 Ω @ 4.5V
 - 4.0 Ω @ 2.5V
 - 6.0 Ω @ 1.8V
 - 10 Ω @ 1.5V
- Very Low Gate Threshold Voltage, 1.0V max
- Low Input Capacitance
- Fast Switching Speed
- Low Input/Output Leakage
- Ultra-Small Surface Mount Package
- ESD Protected Gate
- Lead, Halogen, and Antimony Free By Design/RoHS Compliant (Note 2)
- "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

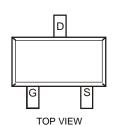
Mechanical Data

- Case: SOT-523
- Case Material: Molded Plastic, "Green" Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminal Connections: See Diagram
- Terminals: Finish Matte Tin annealed over Alloy 42 leadframe.
 Solderable per MIL-STD-202, Method 208
- Marking Information: See Page 4
- Ordering Information: See Page 4
- Weight: 0.002 grams (approximate)









Maximum Ratings @T_A = 25°C unless otherwise specified

Characteristic		Symbol	Value	Unit
Drain Source Voltage		V_{DSS}	20	V
Gate-Source Voltage		V _{GSS}	±10	V
Drain Current (Note 1)		I _D	230	mA
Pulsed Drain Current T	Γ _P = 10μs	I _{DM}	805	mA

Thermal Characteristics @T_A = 25°C unless otherwise specified

Total Power Dissipation (Note 1)	P_{D}	300	mW
Thermal Resistance, Junction to Ambient (Note 1)	$R_{ hetaJA}$	417	°C/W
Operating and Storage Temperature Range	T _J , T _{STG}	-55 to +150	°C

Notes:

- 1. Device mounted on FR-4 PCB, 1 inch x 0.85 inch x 0.062 inch; pad layout as shown on Diodes Inc. suggested pad layout document AP02001, which can be found on our website at http://www.diodes.com/datasheets/ap02001.pdf.
- 2. No purposefully added lead.
- 3. Diodes Inc.'s "Green" policy can be found on our website at http://www.diodes.com/products/lead_free/index.php.

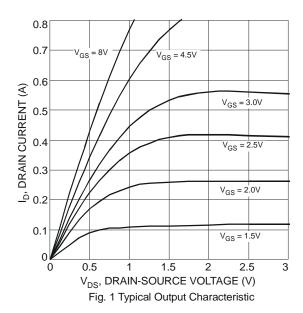


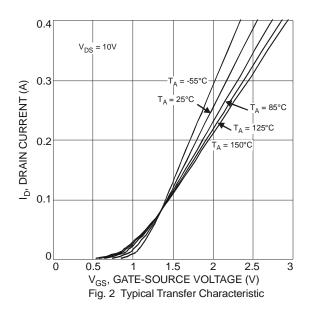
Electrical Characteristics @T_A = 25°C unless otherwise specified

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 4)						
Drain-Source Breakdown Voltage	BV _{DSS}	20	_	_	V	$V_{GS} = 0V$, $I_D = 100 \mu A$
Zero Gate Voltage Drain Current @ T _C = 25°C	C I _{DSS}	_		500	nA	$V_{DS} = 20V, V_{GS} = 0V$
Gate-Body Leakage		_	_	±1 ±500 ±100	μA nA nA	$V_{GS} = \pm 10V, V_{DS} = 0V$ $V_{GS} = \pm 8V, V_{DS} = 0V$
ON CHARACTERISTICS (Note 4)				±100	ПА	$V_{GS} = \pm 5V$, $V_{DS} = 0V$
Gate Threshold Voltage	V _{GS(th)}	0.5	_	1.0	V	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$
Static Drain-Source On-Resistance		_ _ _ _ _	1.8 2.4 2.9 3.7 5.4	3.0 4.0 6.0 10.0 15.0	Ω	$V_{GS} = 4.5V, I_D = 100 \text{mA}$ $V_{GS} = 2.5V, I_D = 50 \text{mA}$ $V_{GS} = 1.8V, I_D = 20 \text{mA}$ $V_{GS} = 1.5V, I_D = 10 \text{mA}$ $V_{GS} = 1.2V, I_D = 1 \text{mA}$
Forward Transconductance	Y _{fs}	_	242	_	mS	$V_{DS} = 10V, I_{D} = 0.1A$
Source-Drain Diode Forward Voltage		0.5	_	1.0	V	$V_{GS} = 0V, I_{S} = 115mA$
DYNAMIC CHARACTERISTICS						
Input Capacitance	C _{iss}	_	14.1		pF	15)()(
Output Capacitance	Coss	_	2.9		pF	V _{DS} = 15V, V _{GS} = 0V -f = 1.0MHz
Reverse Transfer Capacitance	Crss	_	1.6		pF	1 = 1.0ivii iz
SWITCHING CHARACTERISTICS, V _{GS} = 4.5V (Note 5)						
Turn-On Delay Time	t _{d(on)}	_	3.8	_		
Rise Time	t _r		7.9	_	ns	$V_{GS} = 4.5V, V_{DD} = 10V$
Turn-Off Delay Time	t _{d(off)}	_	13.4	_	113	$I_D = 200 \text{mA}, R_G = 2.0 \Omega$
Fall Time	t _f	_	15.2	_		

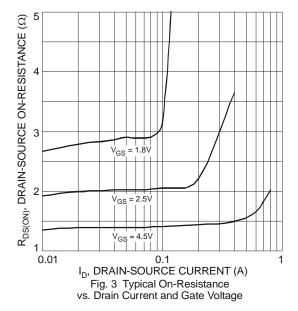
Notes:

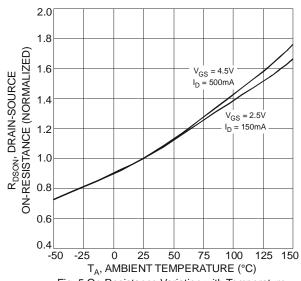
- 4. Short duration pulse test used to minimize self-heating effect.5. Switching characteristics are independent of operating junction temperature.

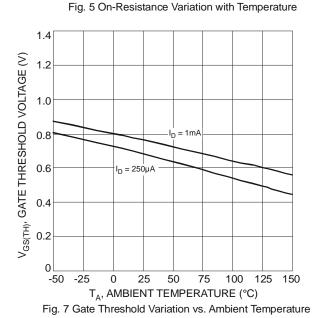












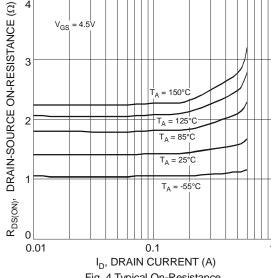


Fig. 4 Typical On-Resistance vs. Drain Current and Temperature

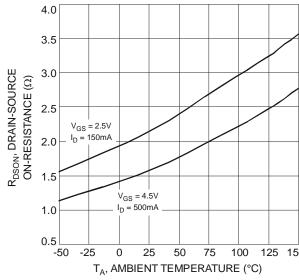


Fig. 6 On-Resistance Variation with Temperature

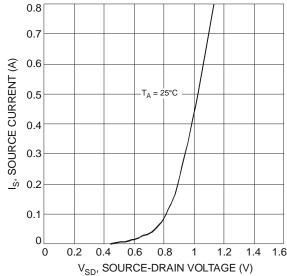
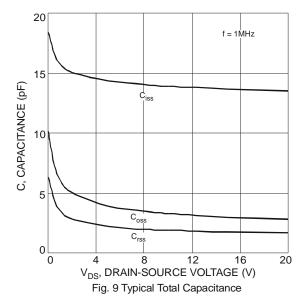


Fig. 8 Diode Forward Voltage vs. Current





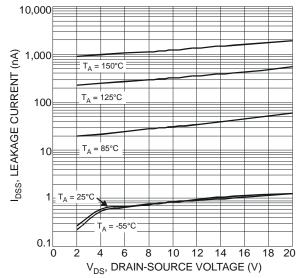
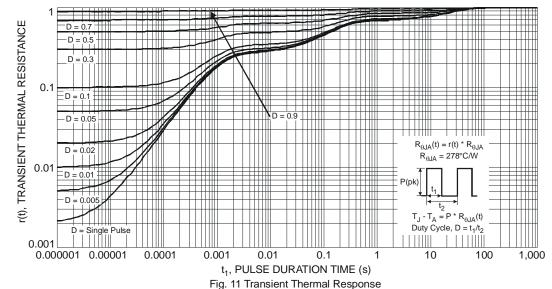


Fig. 10 Typical Leakage Current vs. Drain-Source Voltage

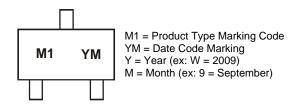


Ordering Information (Note 6)

Part Number	Case	Packaging
DMN26D0UT-7	SOT-523	3,000/Tape & Reel

Notes: 6. For packaging details, go to our website at http://www.diodes.com/datasheets/ap02007.pdf.

Marking Information

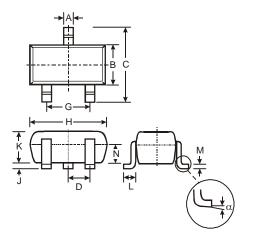


Date Code Key

Year	200	9	2010		2011	20	12	2013		2014	2	2015
Code	W		Х		Υ	2	7	Α		В		С
Month	Jan	Feb	Mar	Apr	May	Jun	Jul	Aug	Sep	Oct	Nov	Dec
Code	1	2	3	4	5	6	7	8	9	0	N	D

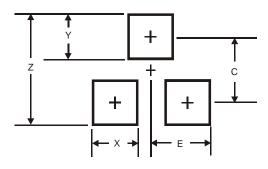


Package Outline Dimensions



	SOT-523						
Dim	Min	Max	Тур				
Α	0.15	0.30	0.22				
В	0.75	0.85	0.80				
С	1.45	1.75	1.60				
D	_	_	0.50				
G	0.90	1.10	1.00				
Н	1.50	1.70	1.60				
J	0.00	0.10	0.05				
K	0.60	0.80	0.75				
L	0.10	0.30	0.22				
M	0.10	0.20	0.12				
N	0.45	0.65	0.50				
α	0°	8°					
All	All Dimensions in mm						

Suggested Pad Layout



Dimensions	Value (in mm)
Z	1.8
Х	0.4
Υ	0.51
С	1.3
F	0.7



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